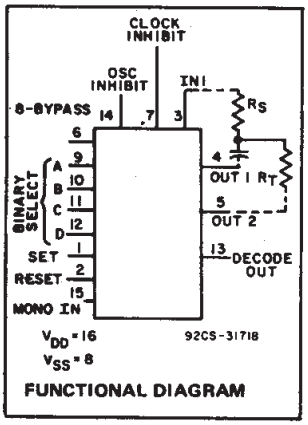
TEXAS INSTRUMENTS
Data sheet acquired from Harris Semiconductor
SCHS083

CD4536B Types

CMOS Programmable Timer

High-Voltage Types (20-Volt Rating)



FUNCTIONAL DIAGRAM

■ CD4536B is a programmable timer consisting of 24 ripple-binary counter stages. The salient feature of this device is its flexibility. The device can count from 1 to 2^{24} or the first 8 stages can be bypassed to allow an output, selectable by a 4-bit code, from any one of the remaining 16 stages. It can be driven by an external clock or an RC oscillator that can be constructed using on-chip components. Input IN1 serves as either the external clock input or the input to the on-chip RC oscillator. OUT1 and OUT2 are connection terminals for the external RC components. In addition, an on-chip monostable circuit is provided to allow a variable pulse width output. Various timing functions can be achieved using combinations of these capabilities.

A logic 1 on the 8-BYPASS input enables a bypass of the first 8 stages and makes stage 9 the first counter stage of the last 16 stages. Selection of 1 of 16 outputs is accomplished by the decoder and the BCD inputs A, B, C and D. MONO IN is the timing input for the on-chip monostable oscillator. Grounding of the MONO IN terminal through a resistor of 10K ohms or higher, disables the one-shot circuit and connects the decoder directly to the DECODE OUT terminal. A resistor to V_{DD} and a capacitor to ground from the MONO IN terminal enables the one-shot circuit and controls its pulse width.

A fast test mode is enabled by a logic 1 on 8-BYPASS, SET, and RESET. This mode divides the 24-stage counter into three 8-stage sections to facilitate a fast test sequence.

The CD4536B types are supplied in 16-lead hermetic dual-in-line ceramic packages (D and F suffixes), 16-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

Features:

- **24 flip-flop stages — counts from 2^0 to 2^{24}**
- **Last 16 stages selectable by BCD select code**
- **Bypass input allows bypassing first 8 stages**
- **On-chip RC oscillator provision**
- **Clock inhibit input**
- **Schmitt-trigger in clock line permits operation with very long rise and fall times**
- **On-chip monostable output provision**
- **Typical f_{CL} = 3 MHz at V_{DD} = 10 V**
- **Test mode allows fast test sequence**
- **Set and reset inputs**
- **Capable of driving two low power TTL loads, one lower-power Schottky load, or two HTL loads over the rated temperature range**
- **Standardized, symmetrical output characteristics**
- **100% tested for quiescent current at 20 V**
- **5-V, 10-V, and 15-V parametric ratings**
- **Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"**

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
Supply-Voltage Range (For T_A = Full Package Temperature Range)	3	18	V

MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltages referenced to V_{SS} Terminal) ..... -0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5V to V_{DD} +0.5V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -55°C to +100°C 500mW
For T_A = +100°C to +125°C ..... Derate Linearity at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
FOR T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)..... 100mW
OPERATING-TEMPERATURE RANGE (T_A) .....-55°C to +125°C
STORAGE TEMPERATURE RANGE (T_{stg}) .....-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 inch (1.59 ± 0.79mm) from case for 10s max ..... +265°C

DECODE OUT SELECTION TABLE

D	C	B	A	NUMBER OF STAGES IN DIVIDER CHAIN	
				8-BYPASS = 0	8-BYPASS = 1
0	0	0	0	9	1
0	0	0	1	10	2
0	0	1	0	11	3
0	0	1	1	12	4
0	1	0	0	13	5
0	1	0	1	14	6
0	1	1	0	15	7
0	1	1	1	16	8
1	0	0	0	17	9
1	0	0	1	18	10
1	0	1	0	19	11
1	0	1	1	20	12
1	1	0	0	21	13
1	1	0	1	22	14
1	1	1	0	23	15
1	1	1	1	24	16

0 = Low Level 1 = High Level

STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS
								+25			
	V_O (V)	V_{IN} (V)	V_{DD} (V)	−55	−40	+85	+125	Min.	Typ.	Max.	
Quiescent Device Current, I_{DD} Max.	–	0,5	5	5	5	150	150	–	0.04	5	μA
	–	0,10	10	10	10	300	300	–	0.04	10	
	–	0,15	15	20	20	600	600	–	0.04	20	
	–	0,20	20	100	100	3000	3000	–	0.08	100	
Output Low (Sink) Current I_{OL} Min.	0.4	0,5	5	0.64	0.61	0.42	0.36	0.51	1	–	mA
	0.5	0,10	10	1.6	1.5	1.1	0.9	1.3	2.6	–	
	1.5	0,15	15	4.2	4	2.8	2.4	3.4	6.8	–	
Output High (Source) Current, I_{OH} Min.	4.6	0,5	5	−0.64	−0.61	−0.42	−0.36	−0.51	−1	–	
	2.5	0,5	5	−2	−1.8	−1.3	−1.15	−1.6	−3.2	–	
	9.5	0,10	10	−1.6	−1.5	−1.1	−0.9	−1.3	−2.6	–	
	13.5	0,15	15	−4.2	−4	−2.8	−2.4	−3.4	−6.8	–	
Output Voltage: Low-Level, V_{OL} Max.	–	0,5	5	0.05				–	0	0.05	V
	–	0,10	10	0.05				–	0	0.05	
	–	0,15	15	0.05				–	0	0.05	
Output Voltage: High-Level, V_{OH} Min.	–	0,5	5	4.95				4.95	5	–	
	–	0,10	10	9.95				9.95	10	–	
	–	0,15	15	14.95				14.95	15	–	
Input Low Voltage V_{IL} Max.	0.5,4.5	–	5	1.5				–	–	1.5	V
	1,9	–	10	3				–	–	3	
	1.5,13.5	–	15	4				–	–	4	
Input High Voltage, V_{IH} Min.	0.5,4.5	–	5	3.5				3.5	–	–	
	1,9	–	10	7				7	–	–	
	1.5,13.5	–	15	11				11	–	–	
Input Current I_{IN} Max.	–	0,18	18	±0.1	±0.1	±1	±1	–	$±10^{-5}$	±0.1	μA

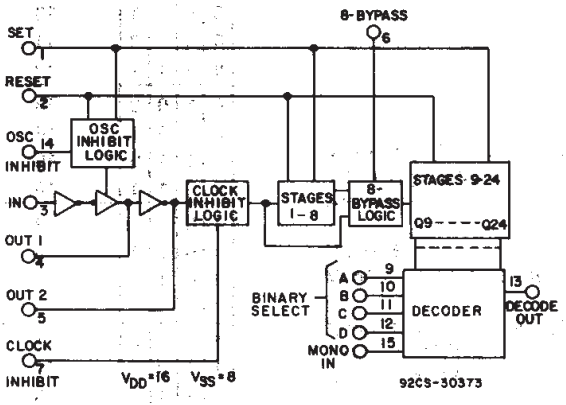


Fig. 1 – Functional block diagram.

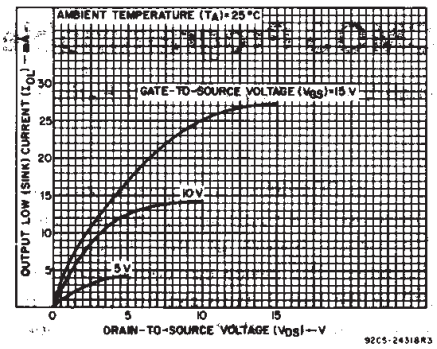


Fig. 2–Typical output low (sink) current characteristics.

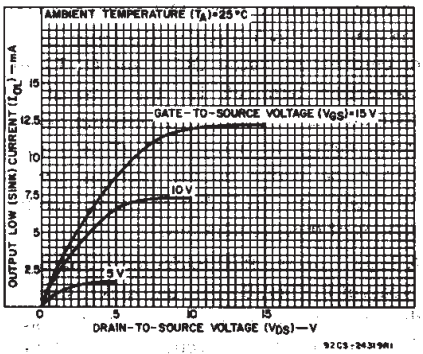


Fig. 3–Minimum output low (sink) current characteristics.

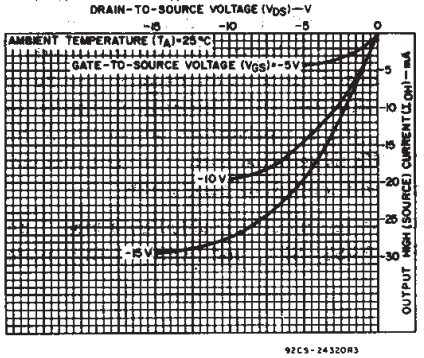


Fig. 4–Typical output high (source) current characteristics.

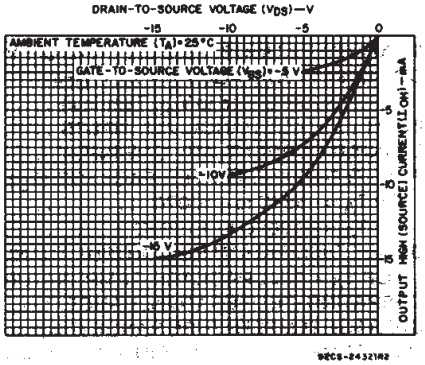


Fig. 5–Minimum output high (source) current characteristics.

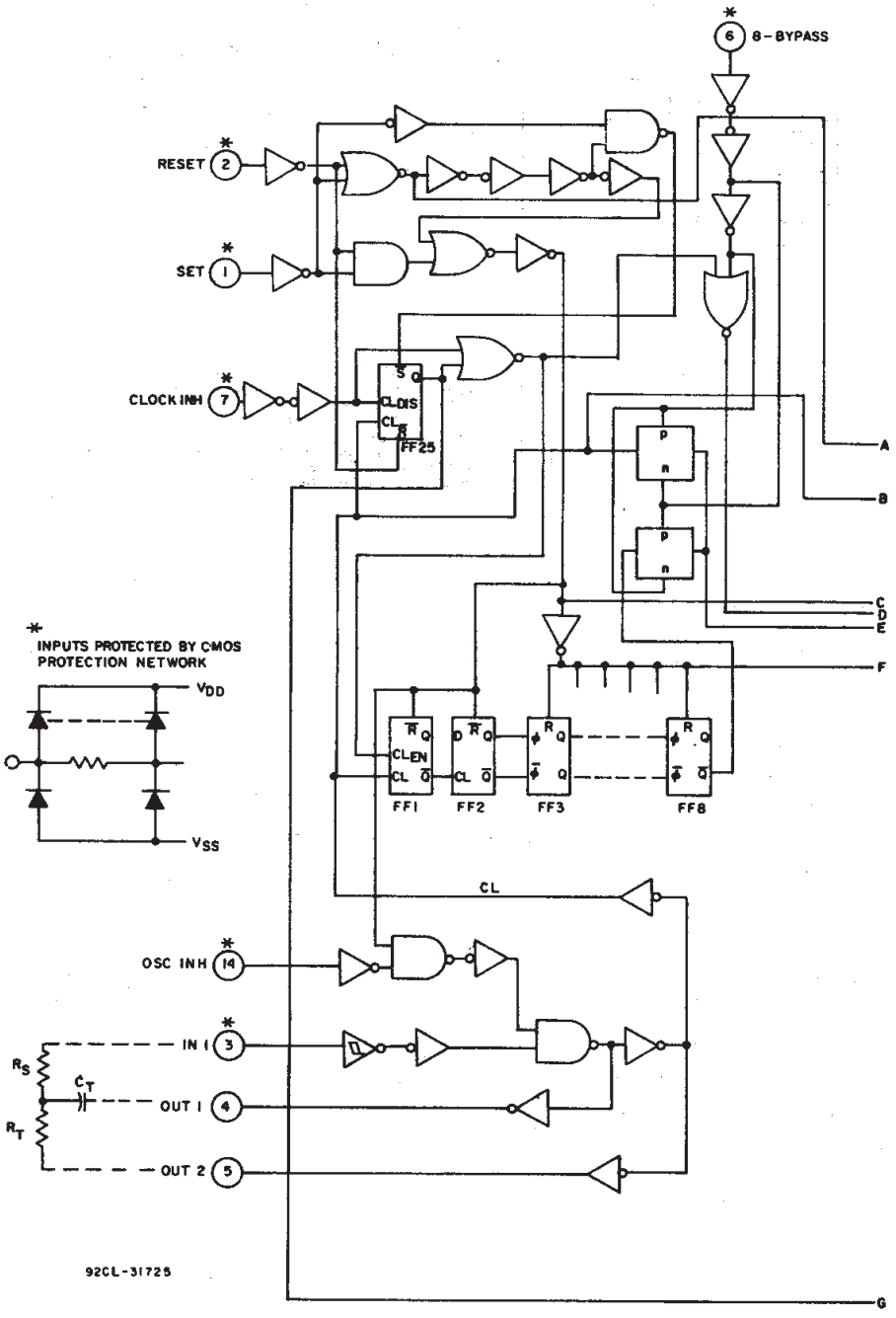


Fig.6 - Logic diagram for CD4536B [*continued on next page*].

NOTE: $f \approx \frac{1}{3R_T C_T}$, $R_S \approx (5 \rightarrow 10) \times R_T$

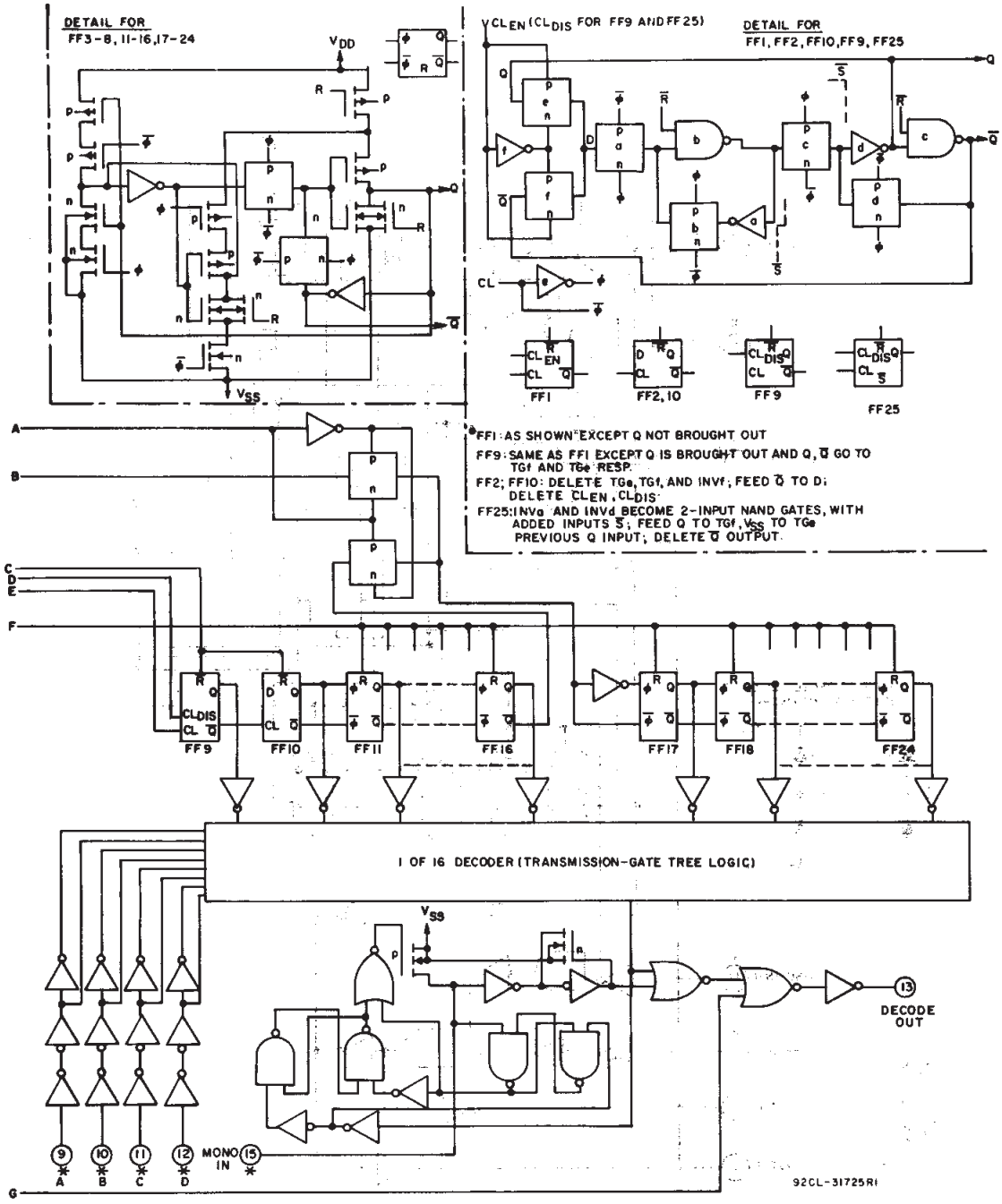
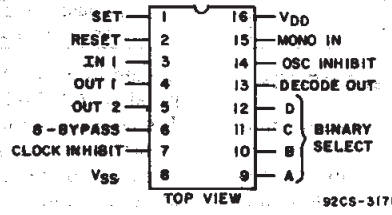


Fig.6 - Logic diagram for CD4536B [continued from previous page].

DYNAMIC ELECTRICAL CHARACTERISTICS, *at $T_A = 25°C$, Input t_r, $t_f = 20$ ns, $C_L = 50$ pF, $R_L = 200$ kΩ*

CHARACTERISTIC	V_{DD} (V)	LIMITS Min.	Typ.	Max.	UNITS
Propagation Delay Times:					
Clock to Q1, 8-Bypass High	5	—	1	2	
	10	—	0.5	1	μs
t_{PHL}, t_{PLH}	15	—	0.35	0.7	
Clock to Q1, 8-Bypass Low	5	—	2.5	5	
	10	—	0.8	1.6	μs
t_{PHL}, t_{PLH}	15	—	0.6	1.2	
Clock to Q16, T_{PHL} t_{PLH}	5	—	4	8	
	10	—	1.5	3	μs
	15	—	1	2	
Q_n to Q_{n+1}, t_{PHL}, t_{PLH}	5	—	150	300	
	10	—	75	150	ns
	15	—	50	100	
Set to Q_n, t_{PLH}	5	—	300	600	
	10	—	125	250	ns
	15	—	80	160	
Reset to Q_n, t_{PHL}	5	—	3	6	
	10	—	1	2	μs
	15	—	0.75	1.5	
Transition Time, t_{THL}, t_{TLH}	5	—	100	200	
	10	—	50	100	ns
	15	—	40	80	
Minimum Pulse Widths:					
Clock	5	—	200	400	
	10	—	75	150	ns
	15	—	50	100	
Set	5	—	200	400	
	10	—	100	200	ns
	15	—	60	120	
Reset	5	—	3	6	
	10	—	1	2	μs
	15	—	0.75	1.5	
Minimum Set Recovery Time,	5	—	2.5	5	
	10	—	1	2	μs
	15	—	0.6	1.6	
Minimum Reset Recovery Time,	5	—	3.5	7	
	10	—	1.5	3	μs
	15	—	1	2	
Maximum Clock Pulse Input Frequency, f_{CL}	5	0.5	1	—	
	10	1.5	3	—	MHz
	15	2.5	5	—	
Maximum Clock Pulse Input Rise or Fall Time, t_r, t_f	5,10,15	Unlimited			μs



Terminal Assignment

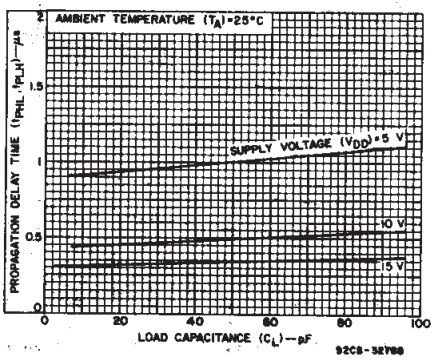


Fig. 7—Typical propagation delay time as a function of load capacitance (CLOCK to Q_1, 8-BYPASS high).

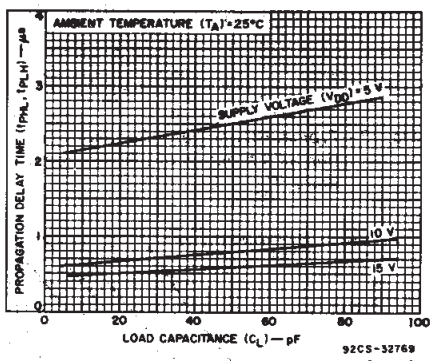


Fig. 8—Typical propagation delay time as a function of load capacitance (CLOCK to Q_1, 8-BYPASS low).

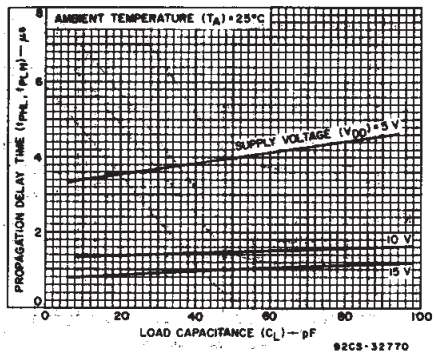


Fig. 9—Typical propagation delay time as a function of load capacitance (CLOCK to Q_{16}, 8-BYPASS high).

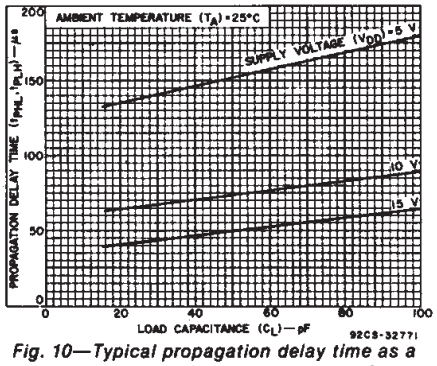


Fig. 10—Typical propagation delay time as a function of load capacitance (Q_N to Q_{N+1}).

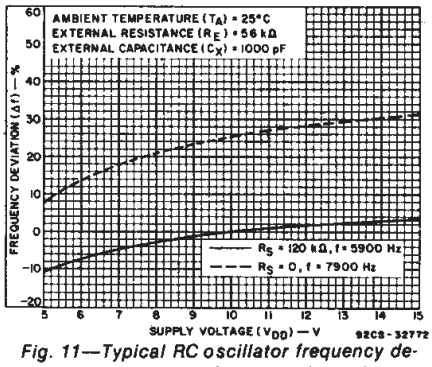


Fig. 11—Typical RC oscillator frequency deviation as a function of supply voltage.

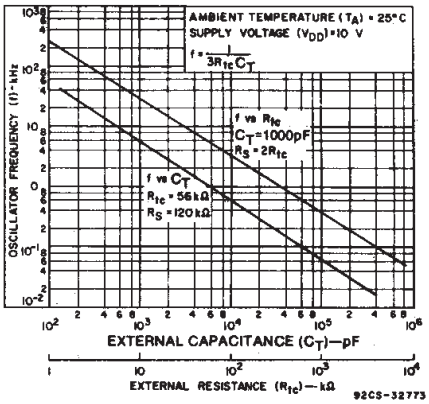


Fig. 12—Typical RC oscillator frequency deviation as a function of time constant resistance and capacitance.

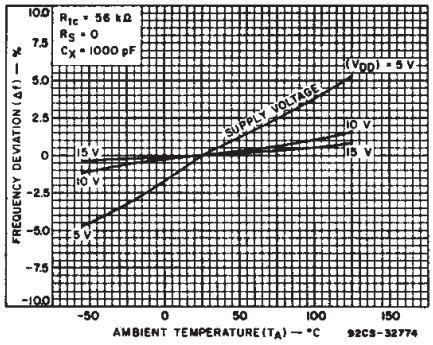


Fig. 13—Typical RC oscillator frequency deviation as a function of ambient temperature (R_S = 0).

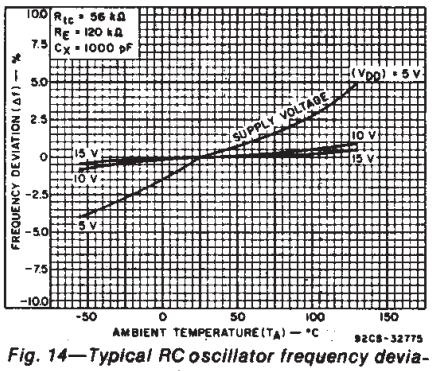


Fig. 14—Typical RC oscillator frequency deviation as a function of ambient temperature (R_S = 120 kΩ).

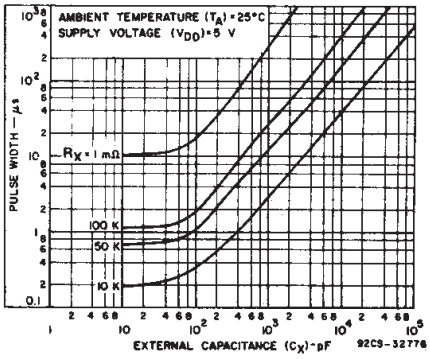


Fig. 15—Typical pulse width as a function of external capacitance (V_{DD} = 5 V).

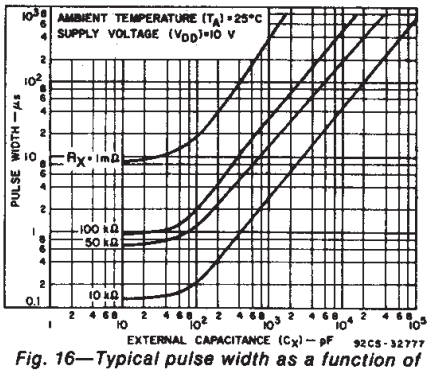


Fig. 16—Typical pulse width as a function of external capacitance (V_{DD} = 10 V).

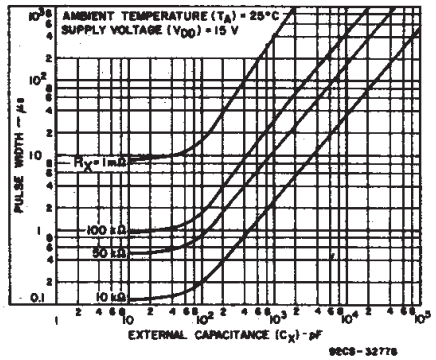


Fig. 17—Typical pulse width as a function of external capacitance (V_{DD} = 15 V).

Functional Test Sequence

Inputs				Outputs	Comments
In_1	Set	Reset	8-Bypass	Decode Out Q1 thru Q24	All 24 steps are in Reset mode
1	0	1	1	0	
1	1	1	1	0	Counter is in three 8-stage section in parallel mode
0	1	1	1	0	First "1" to "0" transition of clock
1 0 — — —	1	1	1		255 "1" to "0" transitions are clocked in the counter
0	1	1	1	1	The 255 "1" to "0" transition
0	0	0	0	1	Counter converted back to 24 stages in series mode Set and Reset must be connected together and simultaneously go from "1" to "0"
1	0	0	0	1	In_1 Switches to a "1"
0	0	0	0	0	Counter Ripples from an all "1" state to an all "0" state

FUNCTIONAL TEST SEQUENCE

Test Function (Figure 23) has been included for the reduction of test time required to exercise all 24 counter stages. This test function divides the counter into three 8-stage sections and 255 counts are loaded in each of the 8-stage sections in parallel. All flip-flops are now at a "1". The counter is now returned to the normal 24-steps in series configuration. One more pulse is entered into In_1 which will cause the counter to ripple from an all "1" state to an all "0" state.

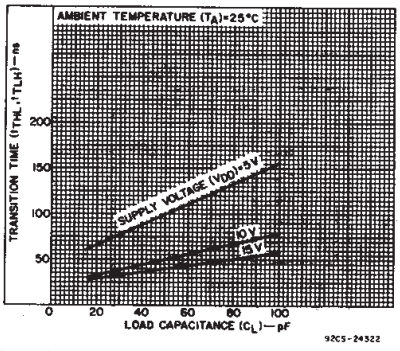


Fig. 18—Typical transition time as a function of load capacitance.

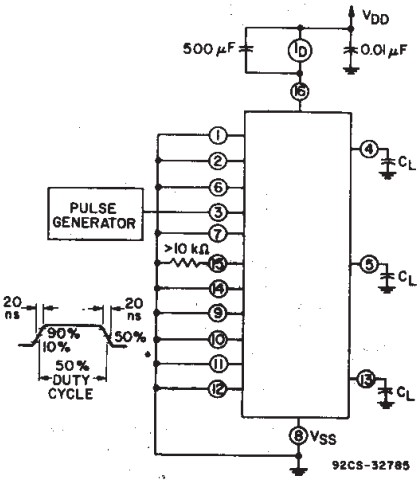


Fig. 20—Dynamic power dissipation test circuit and waveform.

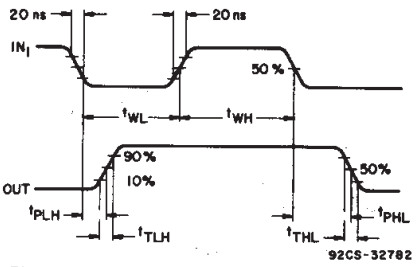


Fig. 22—Input waveforms for switching-time test circuit.

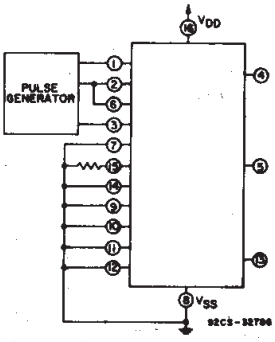
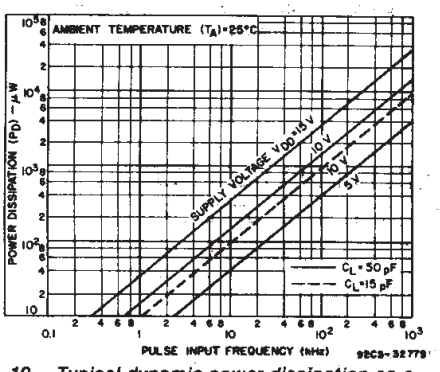


Fig. 23—Functional test circuit.



19 —Typical dynamic power dissipation as a function of input pulse frequency.

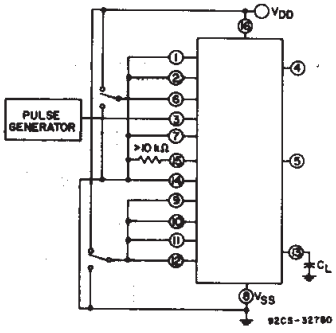


Fig. 21—Switching time test circuit.

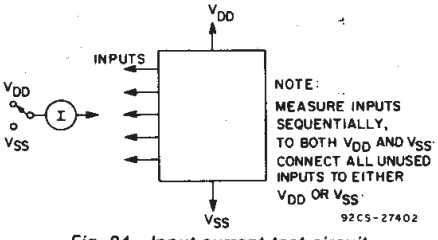


Fig. 24—Input-current test circuit.

TRUTH TABLE

IN1	SET	RESET	CLOCK INH	OSC INH	OUT1	OUT2	DECODE OUT
⌐	0	0	0	0	⌐	⌐	No Change
⌐	0	0	0	0	⌐	⌐	Advance to Next State
X	1	0	0	0	0	1	1
X	0	1	0	0	0	1	0
X	0	0	1	0			No Change
0	0	0	0	X	0	1	No Change
1	0	0	0	⌐	⌐	⌐	Advance to Next State

0 = Low Level 1 = High Level X = Don't Care

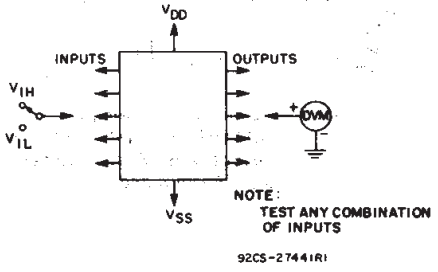


Fig. 25—Input-voltage test circuit.

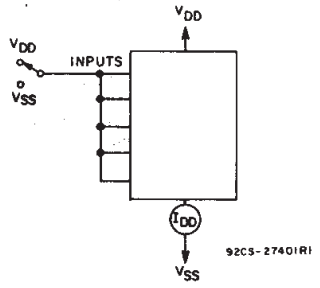


Fig. 26—Quiescent-device current test circuit.

APPLICATIONS

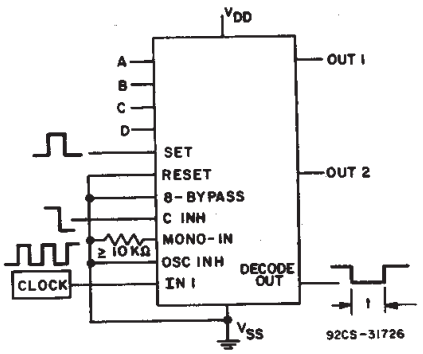


Fig. 27—Time interval configuration using external clock; set and clock inhibit functions.

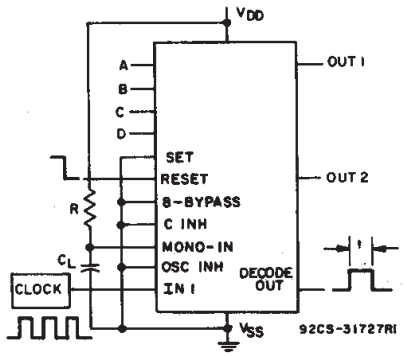


Fig. 28—Time interval configuration using external clock; reset and output monostable to achieve a pulse output.

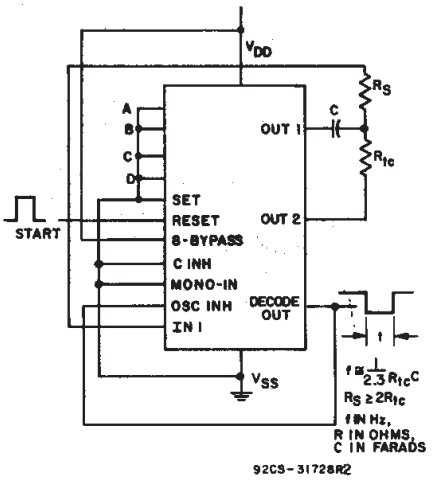


Fig. 29—Time interval configuration using on-chip RC oscillator and reset input to initiate time interval.

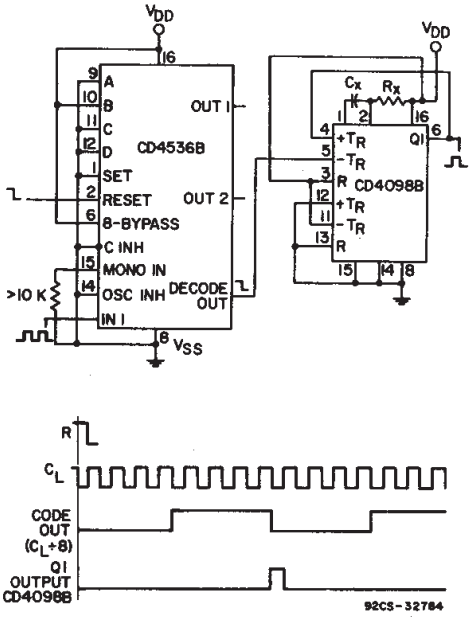


Fig.30 – Application showing use of CD4098B and CD4536B to get decode pulse 8 clock pulses after Reset pulse.

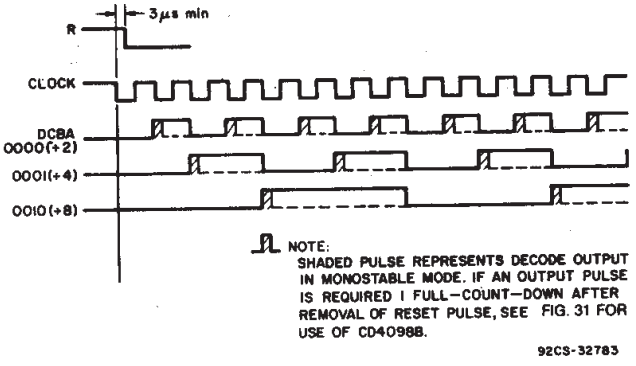
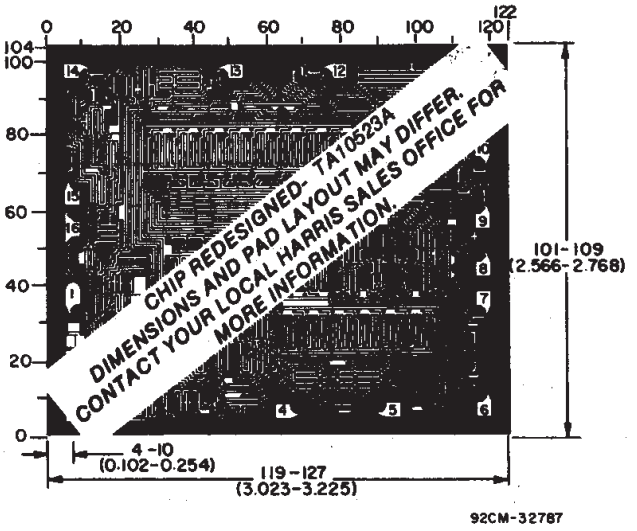


Fig.31 – CD4536B Timing Diagram.

Dimensions and pad layout for CD4536BH.

Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils (10^{-3} inch).



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